

QUANTUM DOT INFRARED PHOTODETECTOR AND METHOD FOR FABRICATING THE SAME

ABSTRACT OF THE DISCLOSURE

- 5 A method for fabricating a quantum dot infrared photodetector by using molecular beam epitaxy is provided. The method includes steps of growing a first gallium arsenide layer as a buffer layer on a gallium arsenide substrate, growing a first undoped aluminum gallium arsenide layer as a blocking layer on the first gallium arsenide layer, growing a
- 10 quantum dot structure layer on the first undoped aluminum gallium arsenide layer at a specific temperature, and growing a second gallium arsenide layer as a contact layer on the quantum dot structure layer.